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2SD1912

2010A

NPN Epitaxial Planar
Silicon Transistor

Low Frequency Power Amp Applications

Ⓔ2336

Features

- Wide ASO (adoption of MBIT process)
- Low saturation voltage
- High reliability

Absolute Maximum Ratings at Ta=25°C

				unit
Collector to Base Voltage	V_{CBO}		60	V
Collector to Emitter Voltage	V_{CEO}		60	V
Emitter to Base Voltage	V_{EBO}		6	V
Collector Current	I_C		3	A
Peak Collector Current	i_{cp}		8	A
Collector Dissipation	P_C		1.75	W
		Tc=25°C	30	W
Junction Temperature	Tj		150	°C
Storage Temperature	Tstg		-55 to +150	°C

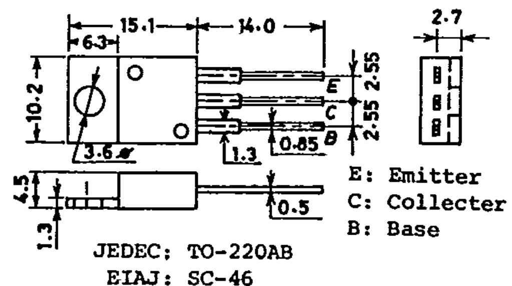
Electrical Characteristics at Ta=25°C

			min	typ	max	unit
Collector Cutoff Current	I_{CBO}	V_{CB}=40V,I_E=0			100	uA
Emitter Cutoff Current	I_{EBO}	V_{EB}=4V,I_C=0			100	uA
DC Current Gain	$h_{FE(1)}$	V_{CE}=5V,I_C=0.5A	70*		280*	
	$h_{FE(2)}$	V_{CE}=5V,I_C=3A	20			
Gain-Bandwidth Product	f_T	V_{CE}=5V,I_C=0.5A		100		MHz
Output Capacitance	c_{ob}	V_{CB}=10V,f=1MHz		40		pF
C-E Saturation Voltage	$V_{CE(sat)}$	I_C=2A,I_B=0.2A		0.4	1	V
Base to Emitter Voltage	V_{BE}	V_{CE}=5V,I_C=0.5A		0.8	1	V
C-B Breakdown Voltage	$V_{(BR)CBO}$	I_C=1mA,I_E=0	60			V
C-E Breakdown Voltage	$V_{(BR)CEO}$	I_C=5mA,R_{BE}=∞	60			V
E-B Breakdown Voltage	$V_{(BR)EBO}$	I_E=1mA,I_C=0	6			V

*: The 2SD1912 is classified by 0.5A h_{FE} as follows:

70 Q 140	100 R 200	140 S 280

Case Outline 2010A
(unit:mm)



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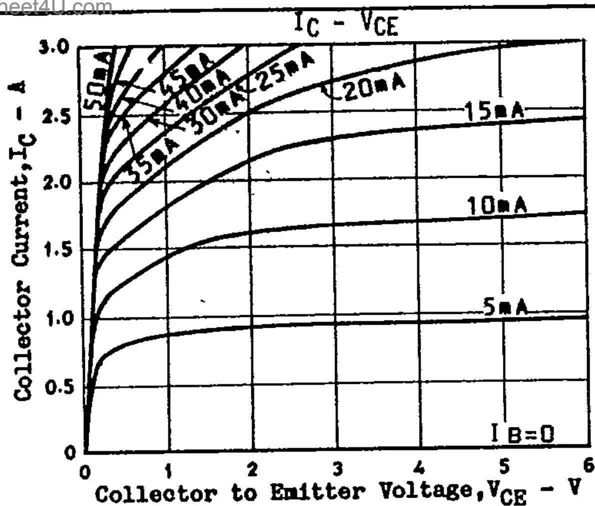

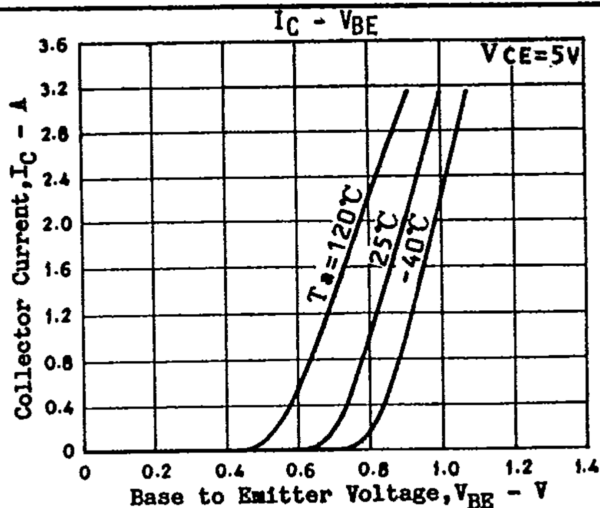

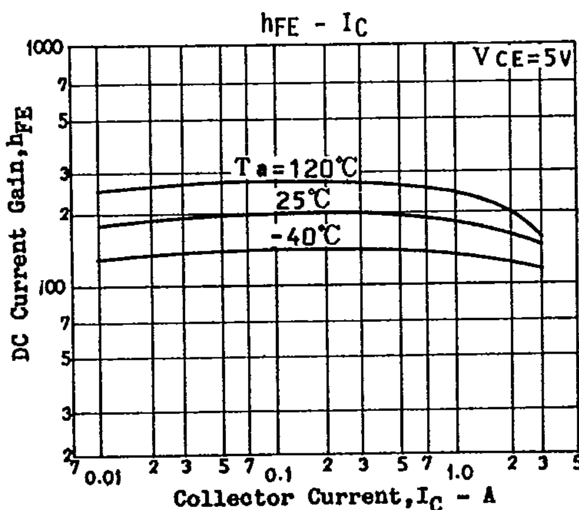

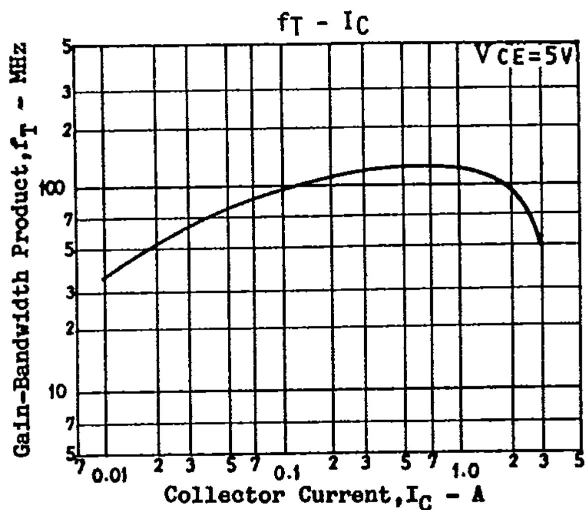

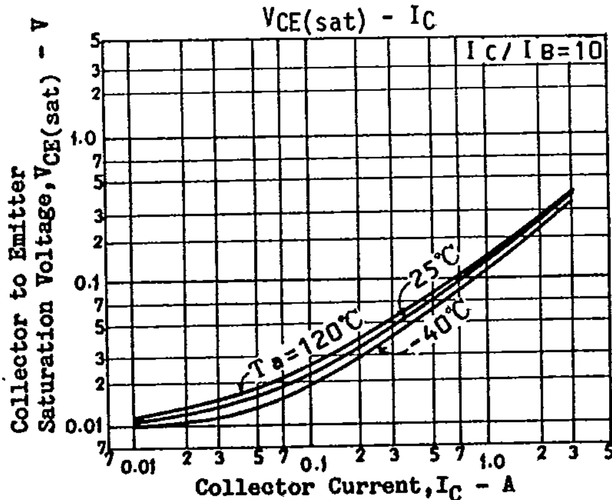

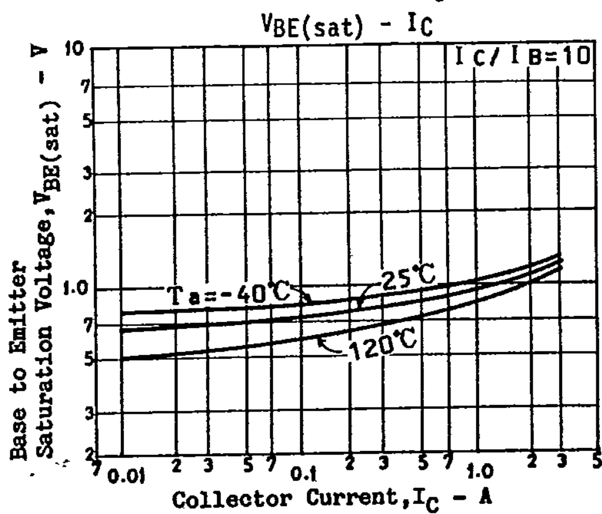

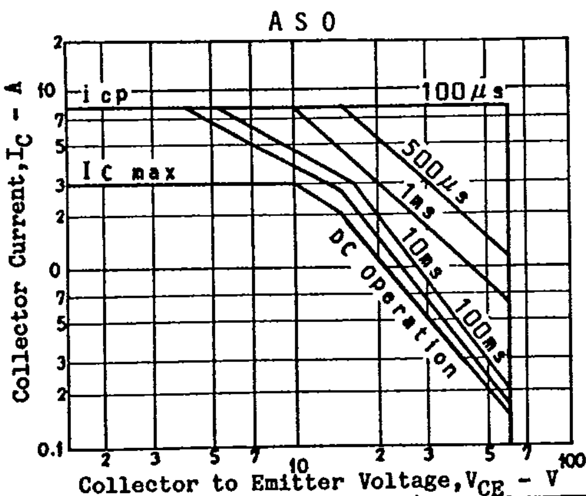

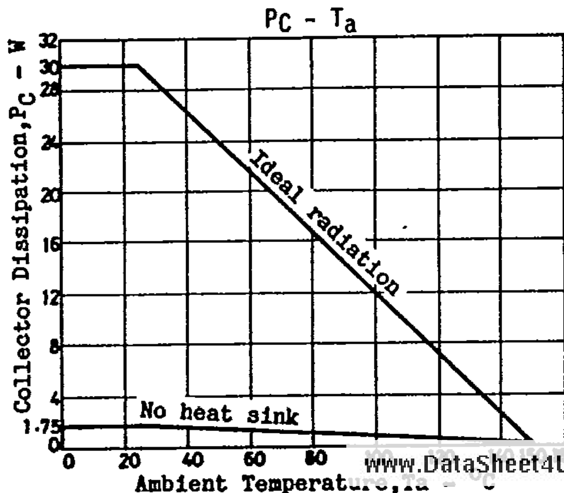

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